

NGT15N65H



N-Channel Enhancement Type IGBT With FRD

Voltage: 650 Volts

Current: 15 Ampers

Package: ITO-220AB

Features

- NH'S Advanced IGBT Technology
- Low Vcesat For Low On-State Loss
- Very Soft Ultra-Fast Recovery Antiparallel Diode
- High Frequency Operation For High Reliability

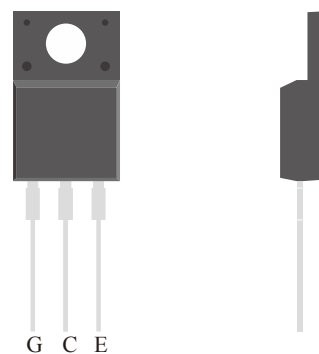
Typical Applications

- Power Factor Correction(PFC)
- Motor Drives
- Uninterruptible Power Supplies(UPS)
- High Frequency Inverters

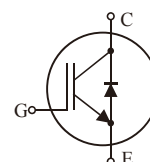
Product Summary

V _{CES} Min.@T _j	650	V
I _C Min.@100℃	15	A
V _{CE(sat)} @25℃	1.5	V

Diagram:



Polarity:



Absolute Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Collector-Emitter Voltage (V _{GS} =0)		V _{CES}	650	V
Gate-Emitter Voltage		V _{GES}	±30	V
Continuous Collector Current (Note 1)	Ta= 25 ℃	I _C	30	A
	Ta= 100 ℃		15	
Drain Current-Pulse (Note 1)	T _j < 175 ℃	I _{CM}	60	A
Maximum Power Dissipation Power	Ta= 25 ℃	P _D	75	W
Dissipation Derating Factor Above 25℃	Ta= 100 ℃		38	
Derating Factor		D _F	0.50	W/℃

Thermal Characteristics (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-50 to 175	℃
Storage Temperature Range		T _{STD}	-50 to 175	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25℃	R _{θJA}	38.5	℃/W
Thermal Resistance Junction-Case(IGBT) With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	2	
Thermal Resistance Junction-Case(FRD) With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	3	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 20).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Collector To Emitter Voltage	VGE=0V, IC=1mA	BV _{CES}	650	--	--	V
Collector To Emitter Leakage Current	VCE= 650 V, VGE=0V, Tj=25℃	I _{CES}	--	--	0.5	uA
	VCE= 520 V, VGE=0V, Tj=125℃		--	0.5	2	mA
Gate To Emitter Leakage Current	VGE= 20 V, VCE=0V	I _{GES}	--	--	250	nA
Emitter To Gate Leakage Current	VGE= -20 V, VCE=0V	I _{EGS}	--	--	250	nA
Forward Transconductance	IC= 7.5 A, VCE= 15 V	gfs	--	5.9	--	S
Static On Characteristics						
Gate Threshold Voltage	VGE= VCE, IC=250uA	V _{GE(TH)}	4.5	5.3	6	V
Collector-Emitter Saturation Voltage	IC= 7.5 A, VGE= 15.0 V, Tj=25℃	V _{CE(SAT)}	--	1.50	2.00	V
	IC= 7.5 A, VGE= 15.0 V, Tj=125℃		--	1.80	--	
Dynamic Characteristics						
Input Capacitance	VCE= 25 V	C _{ies}	--	1123	--	pF
Output Capacitance	VGE= 0 V	C _{oes}	--	44	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{res}	--	4	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.21)						
Turn-On Delay Time	VCE= 312 V IC= 8 A	Tj=25℃	t _{d(on)}	--	8	ns
		Tj=175℃		--	9	
Turn-On Rise Time	VGE= 15.0 V RG= 10 Ω	Tj=25℃	t _r	--	24	ns
		Tj=175℃		--	26	
Turn-Off Delay Time		Tj=25℃	t _{d(off)}	--	66	ns
		Tj=175℃		--	86	
Turn-Off Rise Time		Tj=25℃	t _r	--	76	ns
		Tj=175℃		--	95	
Turn-On Switching Loss	Inductive Load	Tj=25℃	E _{on}	--	28	μJ
Tj=175℃		--		31	--	
Turn-Off Switching Loss		Tj=25℃	E _{off}	--	89	μJ
Tj=175℃		--		111	--	
Total Switching Energy		Tj=25℃	E _{tot}	--	117	μJ
		Tj=175℃		--	142	
Gate Charge Paramters (Test Circuit & Waveform See Fig.22)						
Total Gate Charge	VCE= 312 V	Q _g	--	41	--	nC
Gate-Emitter Charge	VGE= 15 V	Q _{ge}	--	12	--	nC
Gate-Collector Charge	IC= 7.5 A	Q _{gc}	--	15	--	nC

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions		Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.24)							
Max. Diode Forward Cuurent	Tj= 25 °C		I _F	--	--	30.0	A
tp Limited by Tj(max)	Tj= 100 °C			--	--	15.0	
Max. Pulsed Forward Cuurent			I _{SM}	--	--	60	A
Diode Forward Voltage	IF= 15.0 A,VGE=-0V		V _F	--	1.60	2.10	V
Reverse Recovery Time	IF= 7.5 A di/dt= 200 A/us	Tj=25°C	t _{rr}	--	45	--	ns
		Tj=175°C		--	90.0	--	
Reverse Recovery Charge	VGE= 0.0 V VCE= 40 V	Tj=25°C	Q _{rr}	--	142	--	nC
		Tj=175°C		--	475.7	--	
Reverse Recovery Current		Tj=25°C	I _{rrm}	--	6.0	--	A
		Tj=175°C		--	10.6	--	
Reverse Recovery Energy		Tj=25°C	E _{rr}	--	5.4	--	μJ
		Tj=175°C		--	19.1	--	

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Typical Characteristics Curves

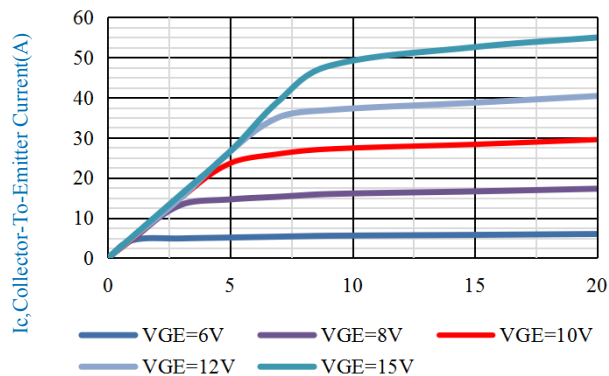


Fig.1-Output Characteristics@Tj=25°C

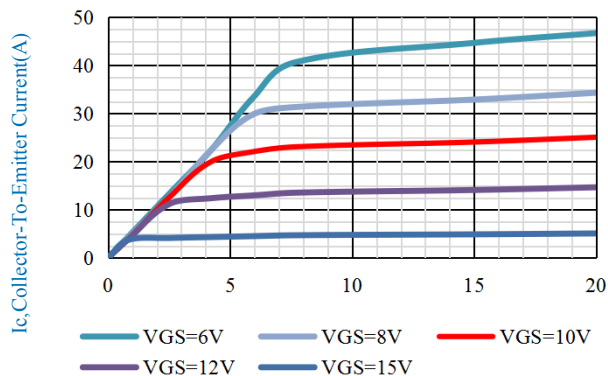


Fig.2-Output Characteristics@Tj=175°C

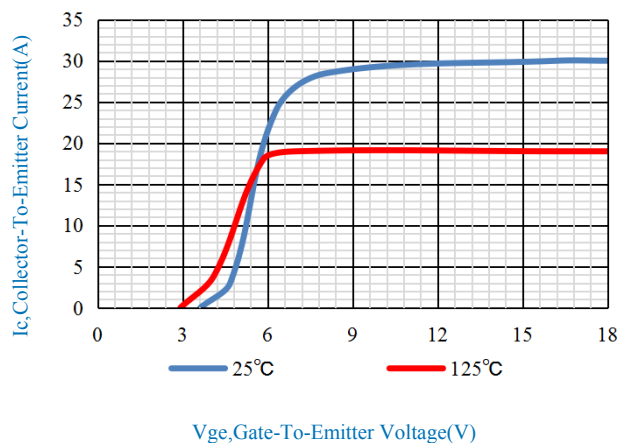


Fig.3-Transfer Characteristics

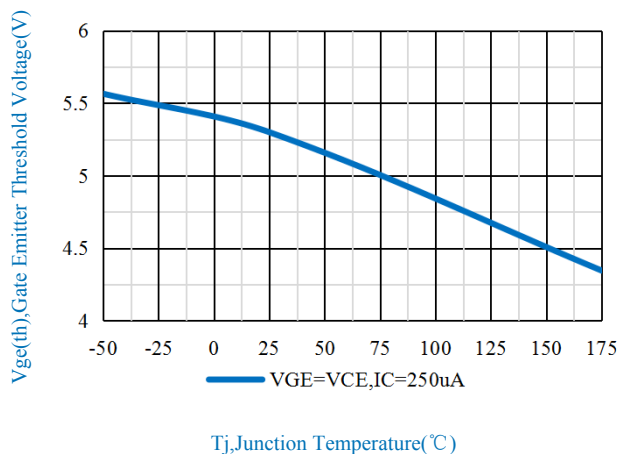


Fig.4-Gate Emitter Threshold Voltage Vs. Junction Temperature

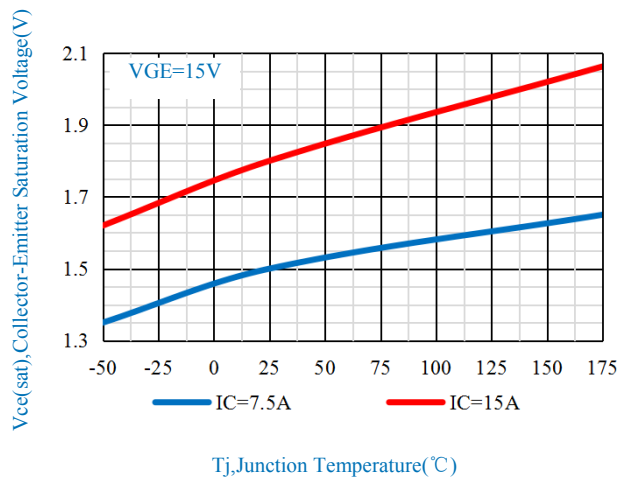


Fig.5-Saturation Voltage vs. Junction Temperature

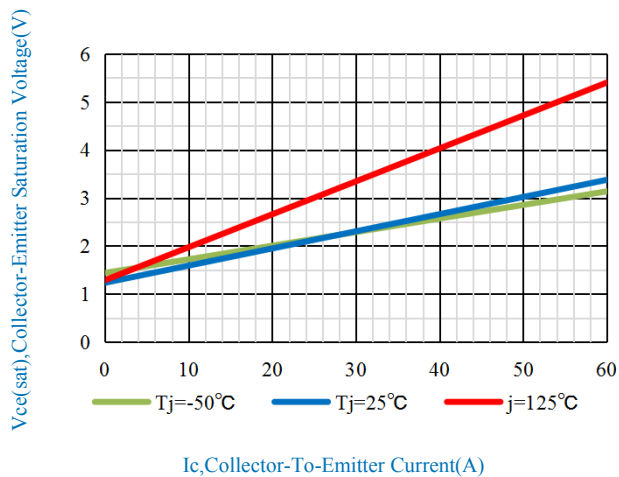


Fig.6-Saturation Voltage vs. Collector-To-Emitter Current

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Typical Characteristics Curves

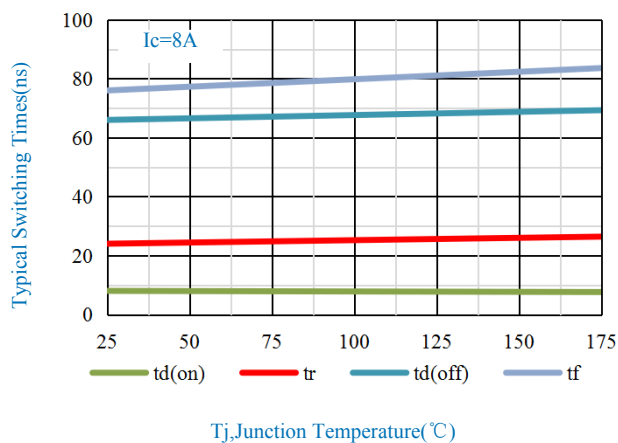


Fig.7-Typical Switching Times Vs. Junction Temperature

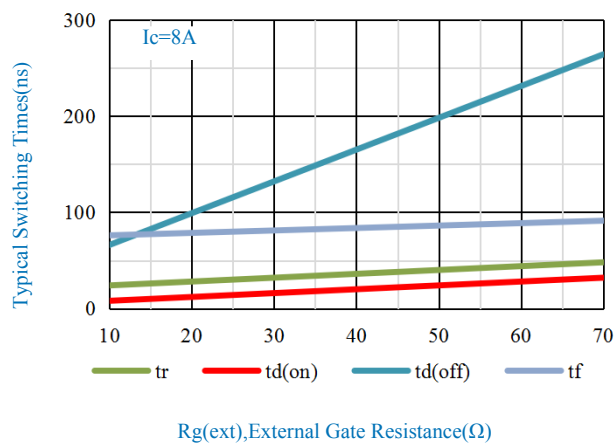


Fig.8-Typical Switching Times Vs. External Gate Resistance

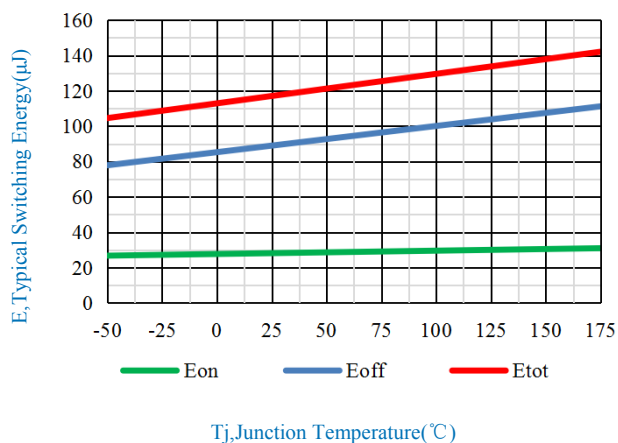


Fig.9-Typical Switching Energy Vs. Junction Temperature

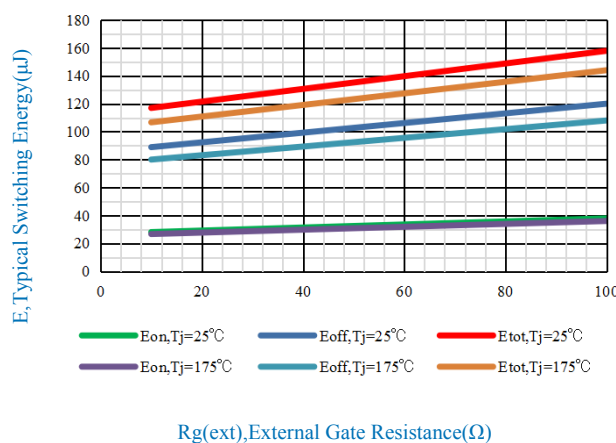


Fig.10-Typical Switching Energy Vs. External Gate Resistance

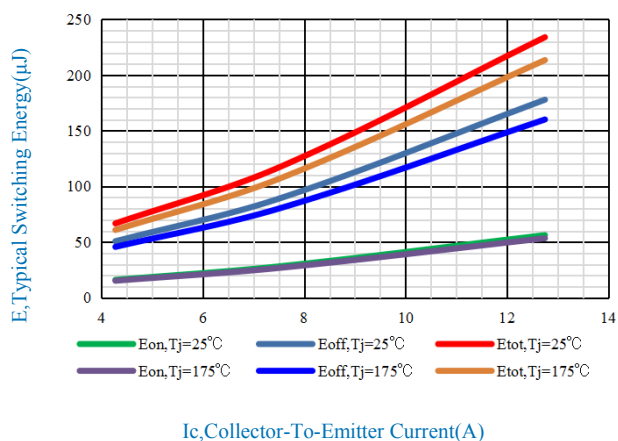


Fig.11-Typical Switching Energy Vs. Collector-To-Emitter Current

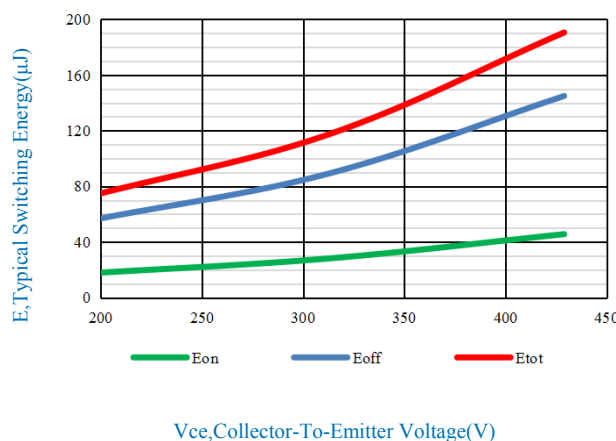


Fig.12-Typical Switching Energy Vs. Collector-To-Emitter Voltage

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Typical Characteristics Curves

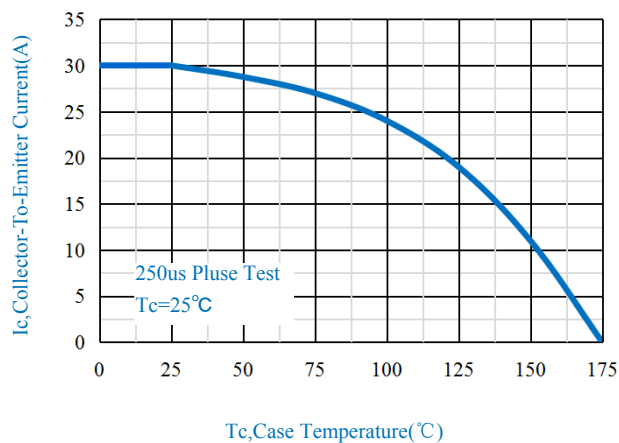


Fig.13-Maximum Continuous Collector Current Vs. Case Temperature

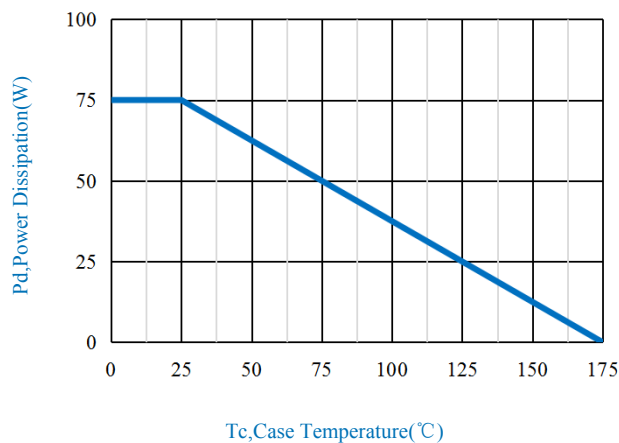


Fig.14-Maximum Power Dissipation Vs. Case Temperature

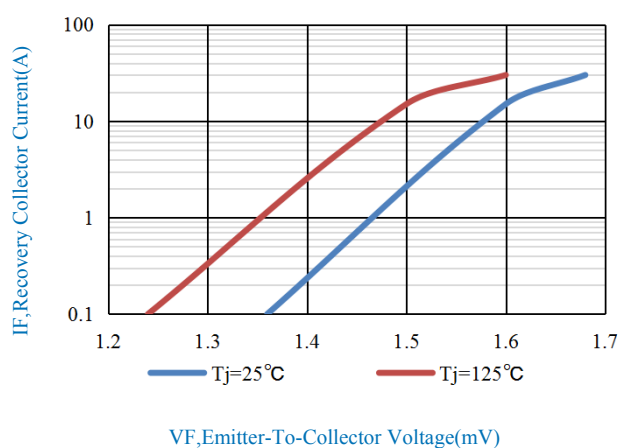


Fig.15-Emitter-To-Collector Diode Forward Voltage

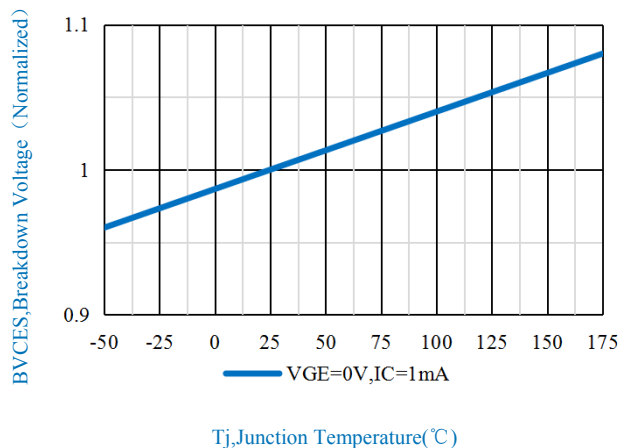


Fig.16-Breakdown Voltage Vs. Junction Temperature

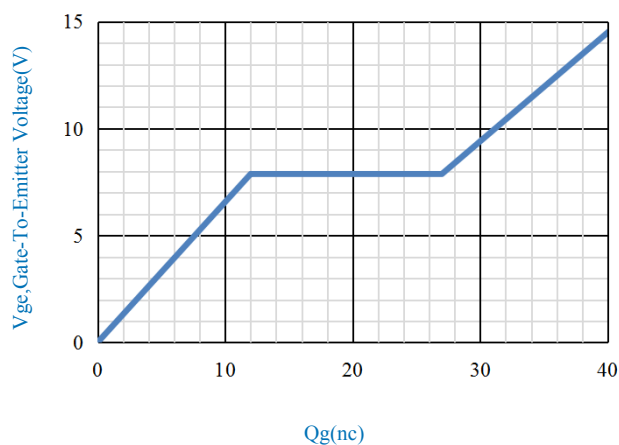


Fig.17-Gate Charge Waveform

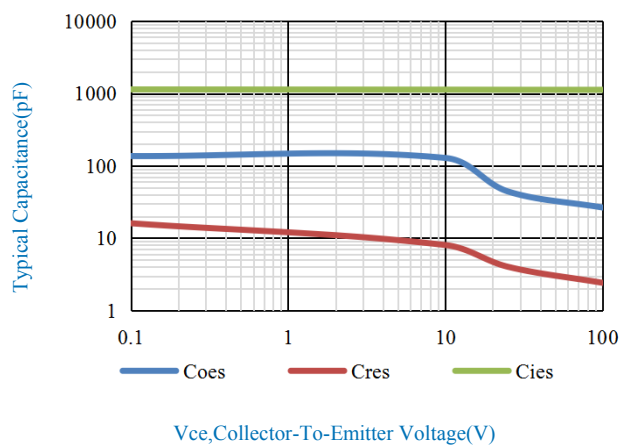


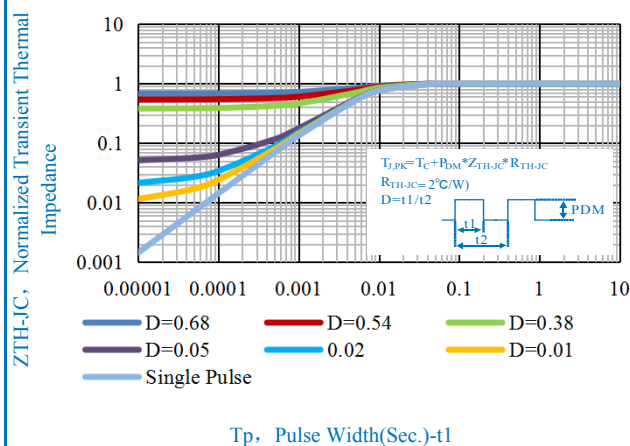
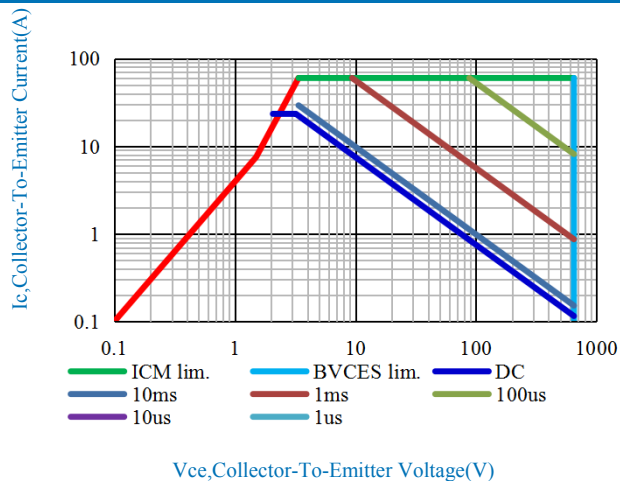
Fig.18-Typical Capacitance Vs. Collector-To-Emitter Voltage

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Typical Characteristics Curves



Test Circuit & Waveform

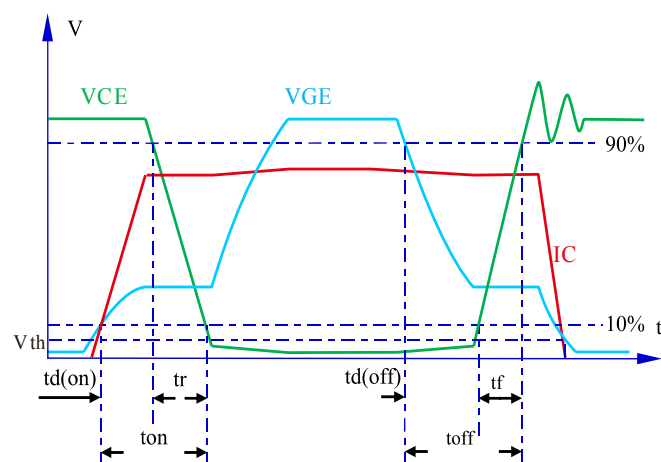
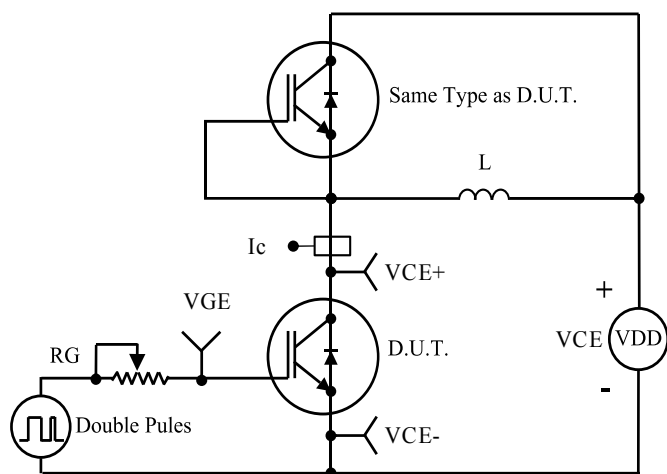


Fig.21- Inductive Switching Test Circuit & Waveform

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N-Channel Enhancement Type IGBT With FRD

Test Circuit & Waveform

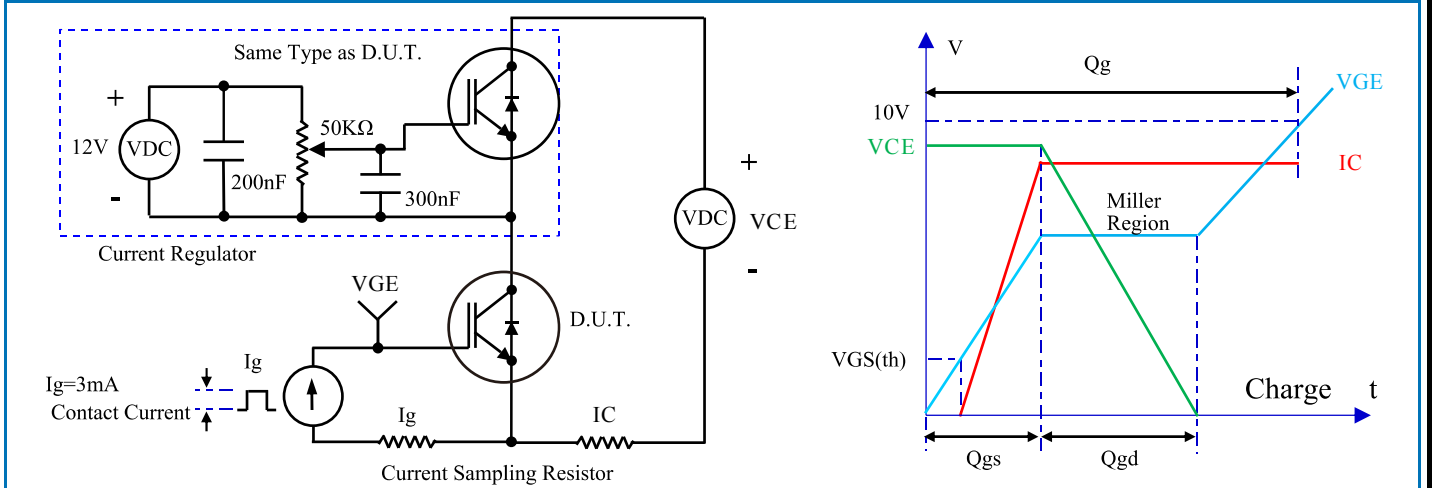


Fig.22-Gate Charge Test Circuit & Waveform

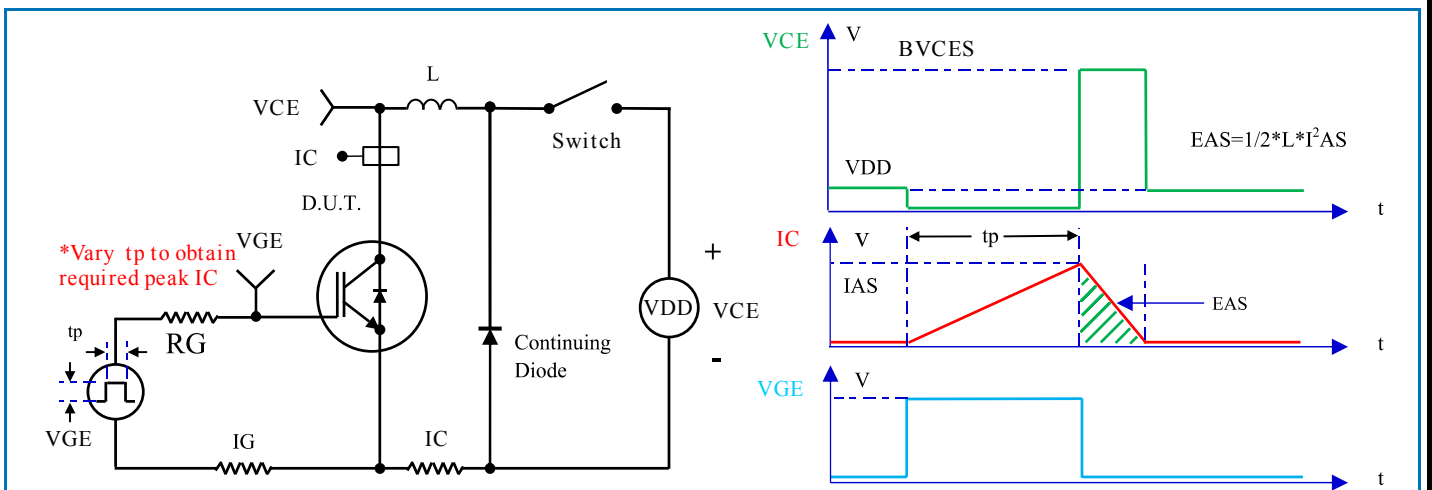


Fig.23- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

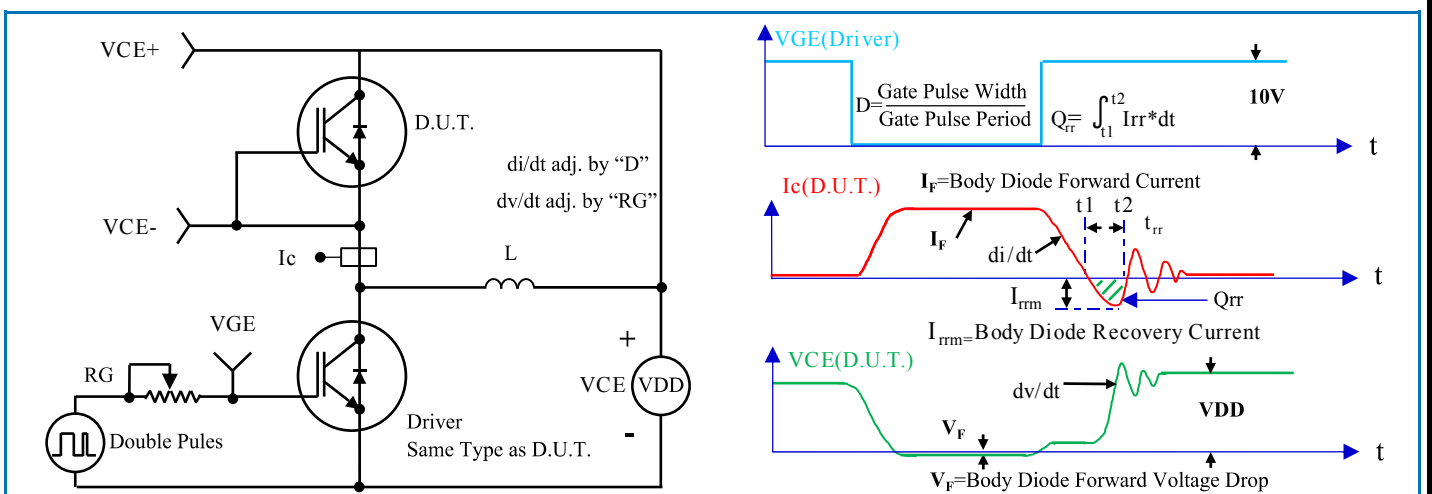


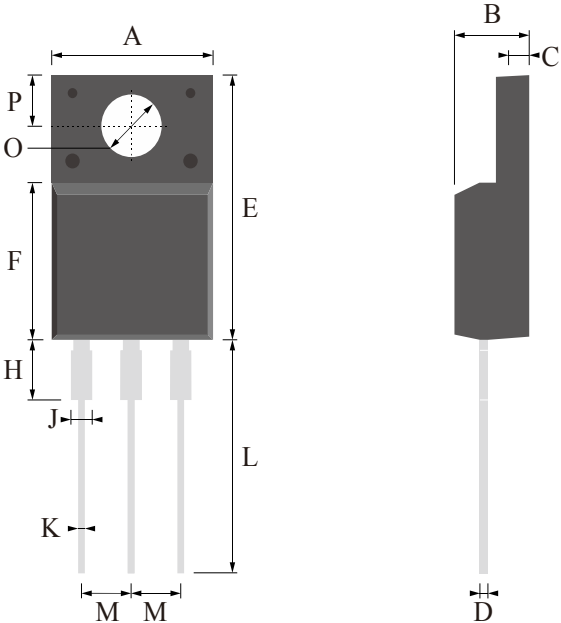
Fig.24- Diode Recovery Test Circuit & Waveform

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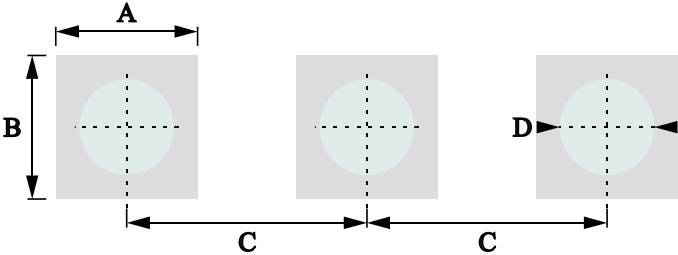
OUTLINE DRAWINGS



ITO-220AB

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.25	-	10.75	0.3642	-	0.4232
B	3.95	-	4.95	0.1555	-	0.1949
C	2.75	-	3.35	0.1083	-	0.1319
D	0.45	-	0.85	0.0177	-	0.0335
E	14.15	-	16.15	0.5571	-	0.6358
F	7.65	-	9.15	0.3012	-	0.3602
L	12.55	-	14.55	0.4941	-	0.5728
H	3.50	-	4.20	0.1378	-	0.1654
J	1.05	-	1.45	0.0413	-	0.0571
K	0.40	-	0.70	0.0157	-	0.0276
M	2.20	-	3.00	0.0866	-	0.1181
O	2.85	-	3.65	0.1122	-	0.1437
P	2.50	-	3.10	0.0984	-	0.1220

RECOMMEDND LAYOUT DRAWINGS



ITO-220AB

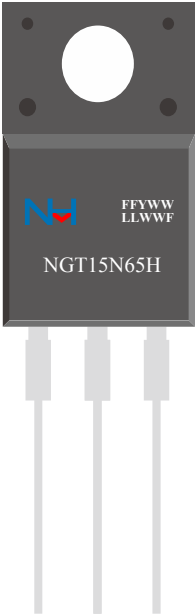
OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.60	-	-	0.0630	-
B	-	1.60	-	-	0.0630	-
C	-	2.54	-	-	0.1000	-
D	-	1.00	-	-	0.0394	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhang Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
NGT15N65H=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
ITO-220AB	P1	1.715	Tube	50	1000	5000

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _{Smin}) -Temperature Max (T _{Smax}) -Time(t _{Smin} to t _{Smax})	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2025-10-20	First Issue		
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